

1. Product Information

1.1 Features

- Surface-mounted package
- Advanced trench cell design

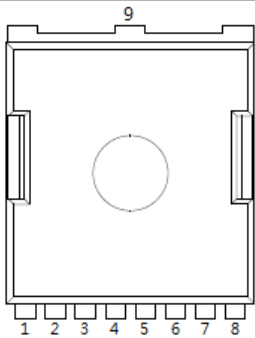
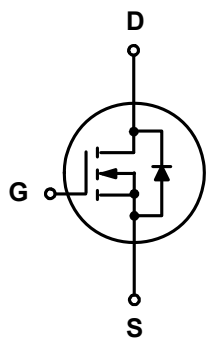
1.2 Applications

- LCD TV appliances
- High power inverter system
- LCDM appliances

1.3 Quick reference

- $BV \geq 100\text{ V}$
- $R_{DS(ON)} \leq 1.25\text{m}\Omega @ V_{GS} = 10\text{ V}$
- $P_{tot} \leq 500\text{ W}$
- $R_{DS(ON)} \leq 2.0\text{m}\Omega @ V_{GS} = 6\text{ V}$
- $I_D \leq 300\text{ A}$

2. Pin Description

Pin	Description	Simplified Outline	Symbol
1	Gate(G)	 <p>Top View TOLL-8</p>	
2,3,4,5,6,7,8	Source(S)		
9	Drain(D)		

3. Maximum Ratings

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	Drain-Source Voltage	$T_C = 25\text{ }^\circ\text{C}$	-	100	V
V_{GS}	Gate-Source Voltage	$T_C = 25\text{ }^\circ\text{C}$	-	± 20	V
I_D^{***}	Drain Current (DC)	$T_C = 25\text{ }^\circ\text{C}, V_{GS} = 10\text{ V}$	-	300	A
		$T_C = 100\text{ }^\circ\text{C}, V_{GS} = 10\text{ V}$	-	282	A
I_{DM}^{*****}	Drain Current (Pulsed)	$T_C = 25\text{ }^\circ\text{C}, V_{GS} = 10\text{ V}$	-	1200	A
P_{tot}	Drain power dissipation	$T_C = 25\text{ }^\circ\text{C}$	-	500	W
T_{stg}	Storage Temperature		-55	150	$^\circ\text{C}$
T_J	Junction Temperature		-	150	$^\circ\text{C}$
I_S	Continuous-Source Current	$T_C = 25\text{ }^\circ\text{C}$	-	300	A
E_{AS}	Single Pulsed Avalanche Energy	$V_{DD}=50\text{V}, L=1.0\text{mH}$	-	2592	mJ
$R_{\theta JA}^{**}$	Thermal Resistance- Junction to Ambient		-	40	$^\circ\text{C/W}$
$R_{\theta JC}^{**}$	Thermal Resistance- Junction to Case		-	0.25	

Notes :

- * Pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
- ** Surface Mounted on minimum footprint pad area.
- *** Limited by bonding wire

4. Ordering Information

Device	Package	Packing
AICN009N10	TOLL-8	Tape & Reel

5. Electrical Characteristics ($T_A=25^\circ$ Unless Otherwise Noted)

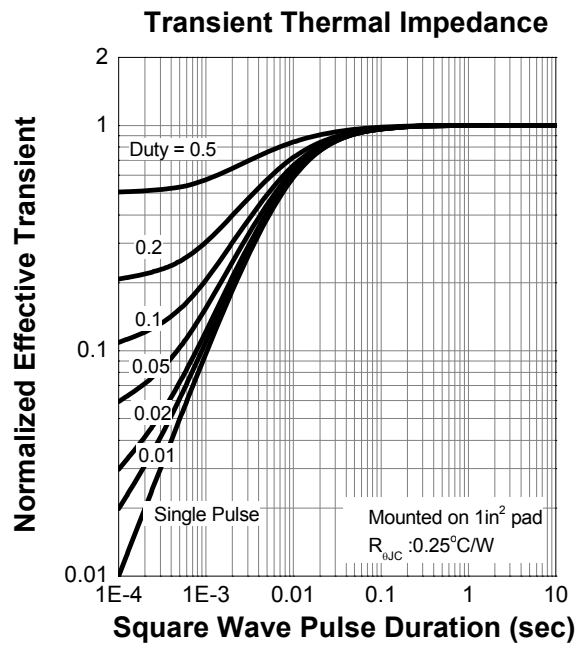
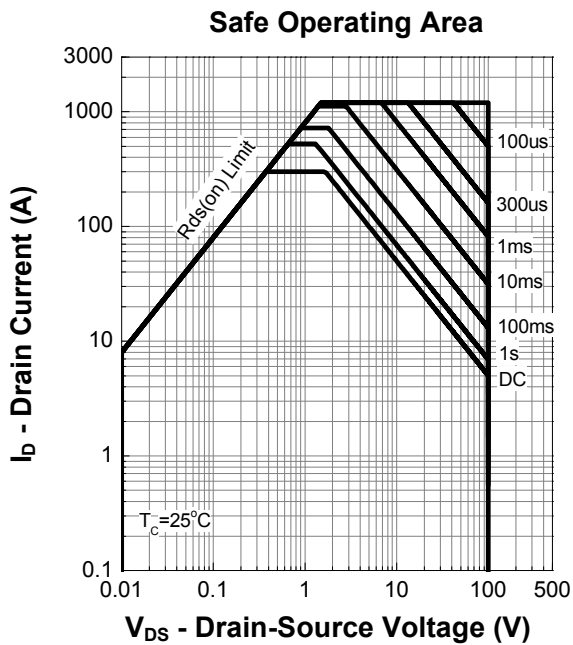
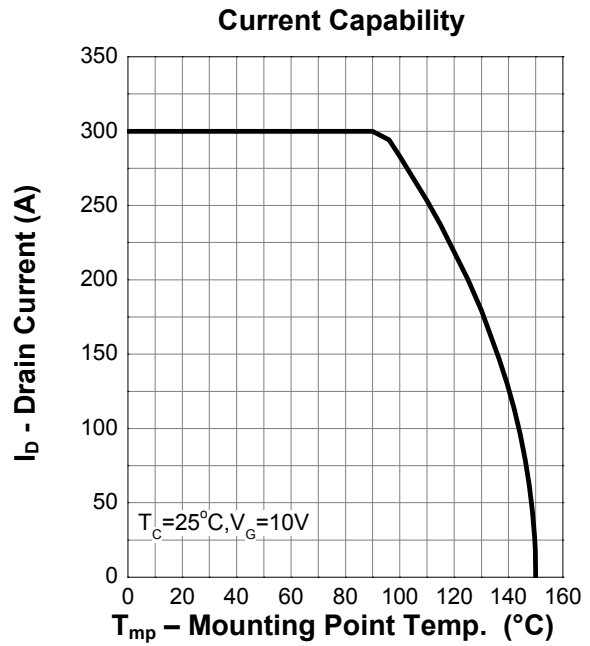
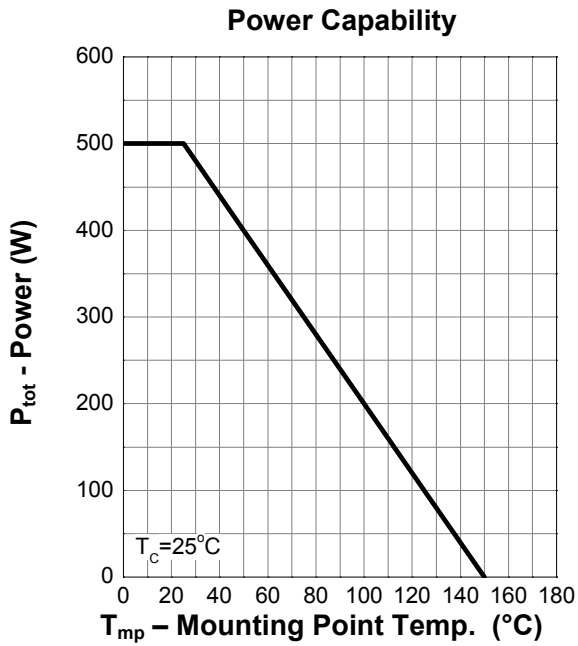
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_{DS} = 250\ \mu\text{A}$	100	-	-	V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{DS} = 250\ \mu\text{A}$	2	-	4	V
I_{DSS}	Drain Leakage Current	$V_{DS} = 80\text{ V}, V_{GS} = 0\text{ V}$	-	-	1	μA
I_{GSS}	Gate Leakage Current	$V_{GS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$	-	-	± 100	nA
$R_{DS(on)}^a$	On-State Resistance	$V_{GS} = 10\text{ V}, I_{DS} = 30\text{ A}$	-	1.05	1.25	m Ω
		$V_{GS} = 6\text{ V}, I_{DS} = 20\text{ A}$	-	1.5	2.0	
Diode Characteristics						
V_{SD}^a	Diode Forward Voltage	$I_{SD} = 30\text{ A}, V_{GS} = 0\text{ V}$	-	-	1.3	V
t_{rr}	Reverse Recovery Time	$I_{DS} = 30\text{ A}, V_{GS} = 0\text{ V}$ $di_{SD}/dt = 100\text{ A}/\mu\text{s}$	-	121	-	nS
Q_{rr}	Reverse Recovery Charge		-	405	-	nC
Dynamic Characteristics^b						
C_{iss}	Input Capacitance	$V_{GS} = 0\text{ V}, V_{DS} = 50\text{ V}$ Frequency = 1 MHz	-	13766	-	pF
C_{oss}	Output Capacitance		-	2155	-	
C_{riss}	Reverse Transfer Capacitance		-	100	-	
$t_{d(on)}$	Turn-on Delay Time	$V_{DS} = 50\text{ V}, V_{GEN} = 10\text{ V},$ $R_G = 3.9\ \Omega, R_L = 1.66\ \Omega,$ $I_{DS} = 30\text{ A}$	-	36	-	nS
t_r	Turn-on Rise Time		-	85	-	
$t_{d(off)}$	Turn-off Delay Time		-	182	-	
t_f	Turn-off Fall Time		-	113	-	
Gate Charge Characteristics^b						
Q_g	Total Gate Charge	$V_{DS} = 50\text{ V}, V_{GS} = 10\text{ V},$ $I_{DS} = 30\text{ A}$	-	284	-	nC
Q_{gs}	Gate-Source Charge		-	73	-	
Q_{gd}	Gate-Drain Charge		-	85	-	

Notes :

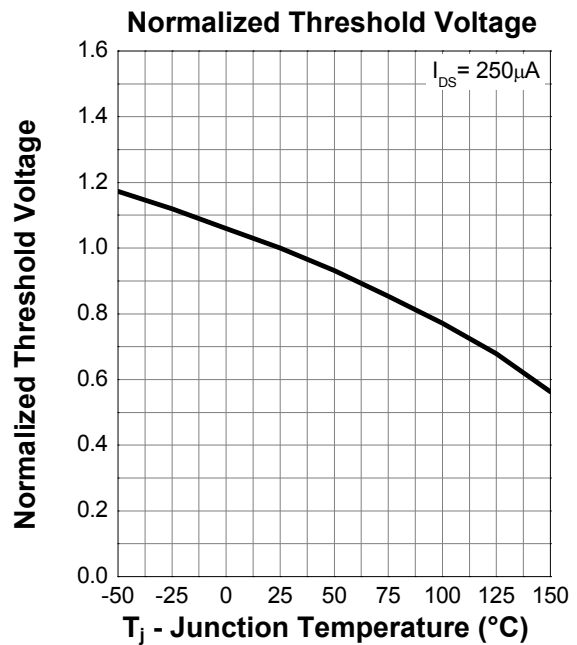
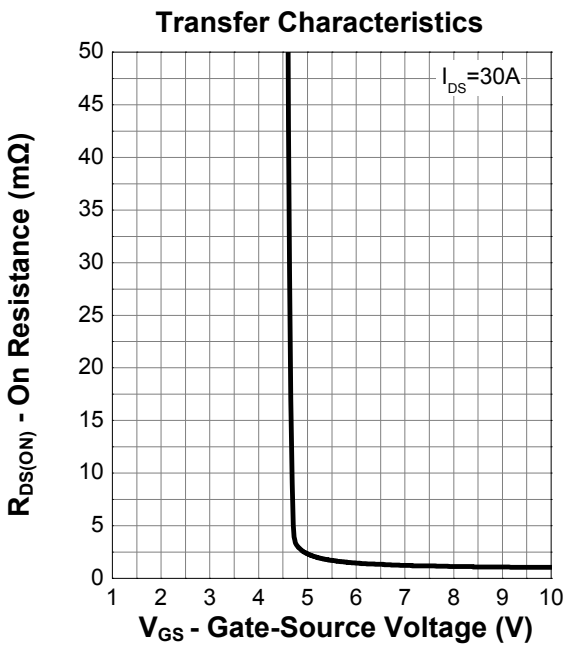
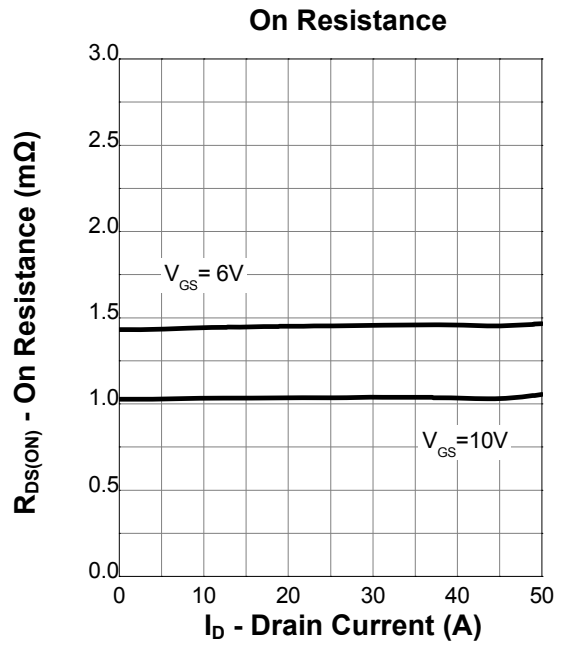
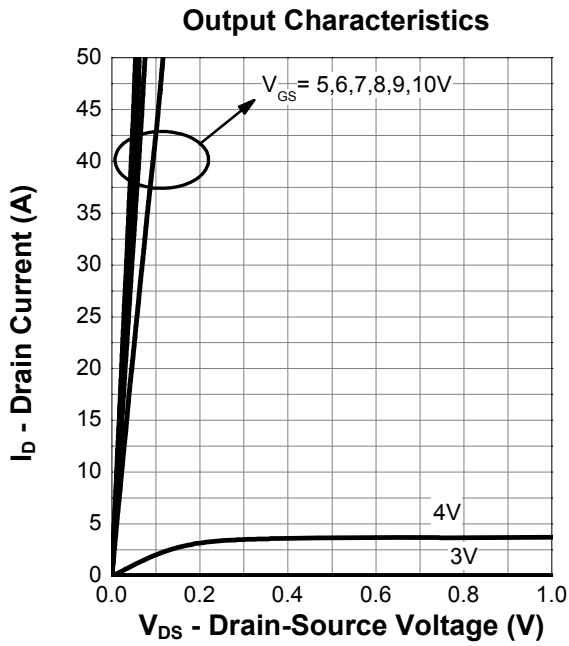
a : Pulse test ; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$

b : Guaranteed by design, not subject to production testing

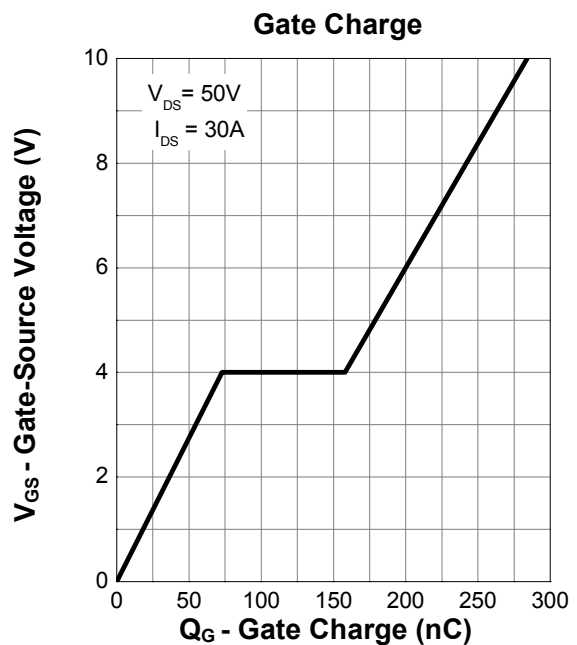
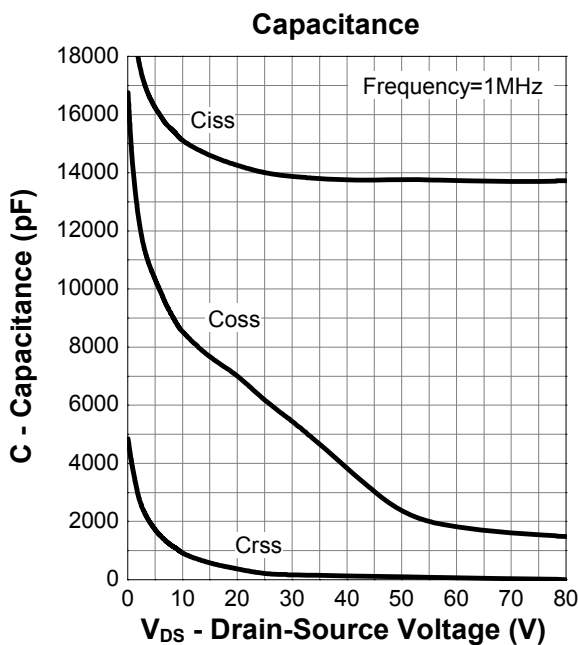
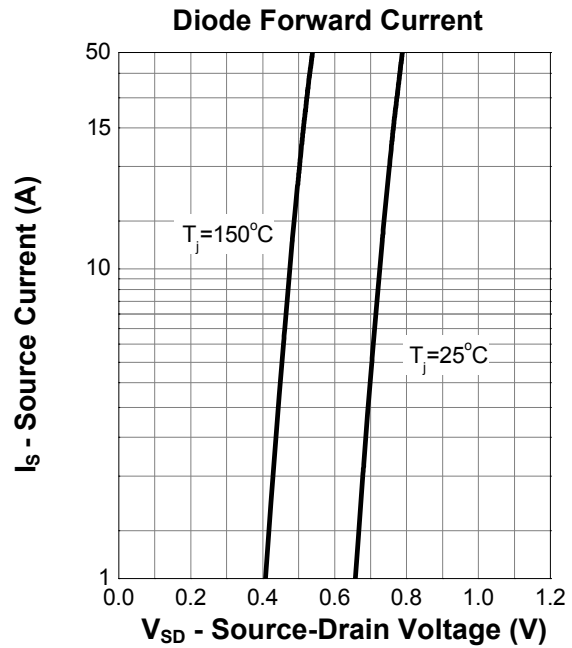
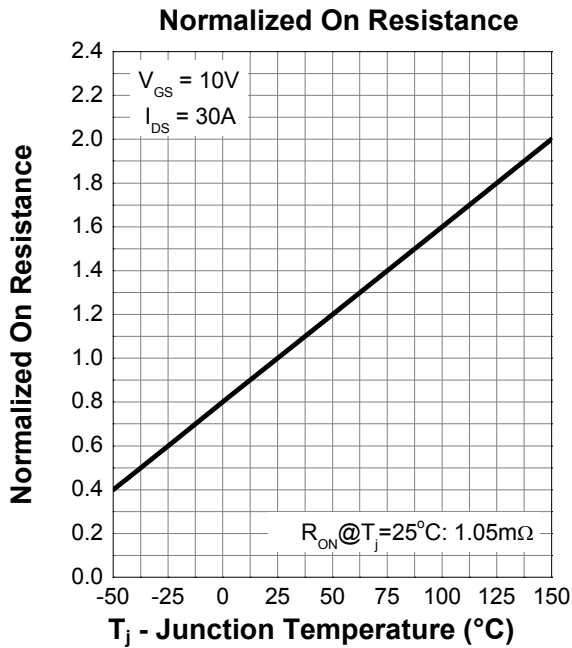
6. Typical Characteristics



6. Typical Characteristics (cont.)

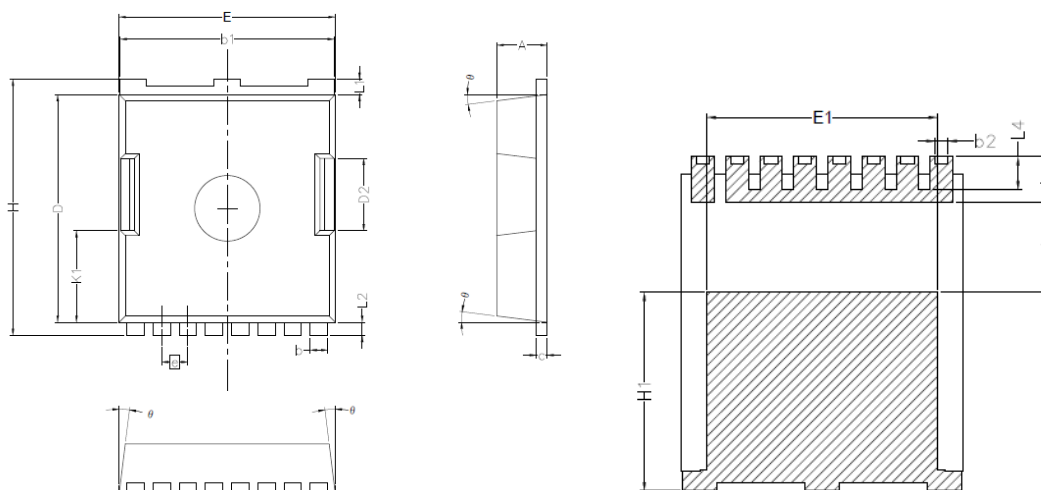


6. Typical Characteristics (cont.)



7. Package Dimensions

TOLL-8 Package



Symbol	Dimensions In Millimeters	
	MIN.	MAX.
A	2.20	2.40
b	0.90	0.90
b1	9.70	9.90
b2	0.42	0.50
c	0.40	0.60
D	10.28	10.58
D2	3.10	3.50
E	9.70	10.10
E1	7.90	8.30
e	1.20BSC	
H	11.48	11.88
H1	6.75	7.15
N	8	
J	3.00	3.30
K1	3.98	4.38
L	1.40	1.80
L1	0.60	0.80
L2	0.50	0.70
L4	1.00	1.30
θ	4°	10°



Note:

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